TRW54601

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TRW54601** is Designed for General Purpose Oscillator Applications up to 2.3 GHz.

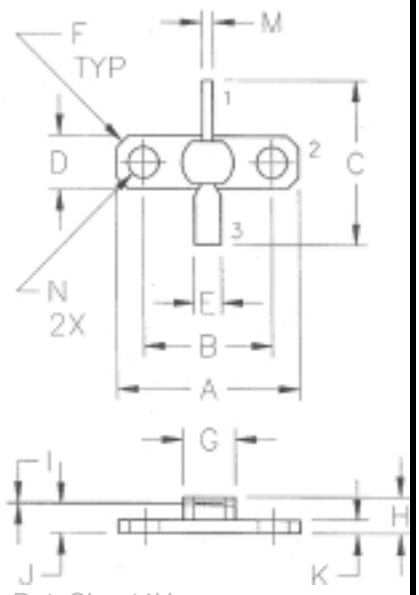
FEATURES:

- Diffused Ballast Resistors
- ***Omnigold***™ Metalization System
- Common Emitter

MAXIMUM RATINGS

I_C	400 mA
V_{CES}	50 V
P_{DISS}	3.0 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	35 °C/W

PACKAGE STYLE .280 4L STUD



DIM	MILLIMETER	TOL	INCHES	TOL
A	20.32	.13	.800	.005
B	14.27	.13	.562	.005
C	18.03	MIN	.710	MIN
D	5.84	.13	.230	.005
E	3.05	.13	.120	.005
F	1.27 x 45°	.13	.005x45°	.005
G	5.84	.13	.230	.005
H	4.57	REF	.180	REF
I	0.13	.02	.005	.001
J	3.30	.13	.130	.005
K	1.52	.13	.060	.005
M	1.27	.13	.050	.005
N	3.30 DIA	.13	.130 DIA	.005

1 = COLLECTOR 2 = EMITTER 3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 10 mA			22			V
BV_{CES}	I_C = 10 mA			50			V
BV_{EBO}	I_E = 1.0 mA			3.5			V
I_{CBO}	V_{CB} = 28 V					0.5	mA
h_{FE}	V_{CE} = 5.0 V	I_C = 100 mA		20			---
C_{OB}	V_{CB} = 28 V		f = 1.0 MHz		2.4	3.0	pF
P_G	V_{CE} = 20 V	I_C = 120 mA	f = 2.3 GHz	8.5	9.5		dB
VSRW	P_{OUT} = 0.5 W					30:0	---

Specifications are subject to change without notice.